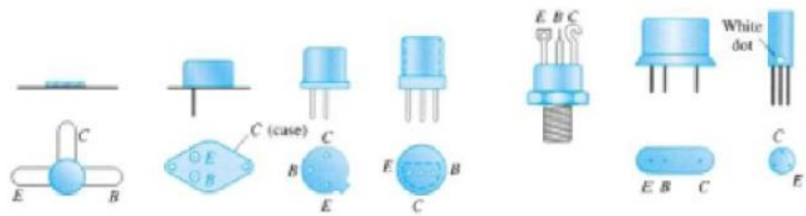


Bipolar Junction Transistors

Instructor

Nasser Ismail

The First Transistor

Co-inventors of the first transistor at Bell Laboratories: Dr. William Shockley (seated); Dr. John Bardeen (left); Dr. Walter H. Brattain. (Courtesy of AT&T Archives.)

Dr. Shockley — Born: London, England, 1910; PhD Harvard, 1936

Dr. Bardeen — Born: Madison, Wisconsin, 1908; PhD Princeton, 1936

Dr. Brattain — Born: Amoy, China, 1902; PhD University of Minnesota, 1928

All shared the Nobel Prize in 1956 for this contribution.

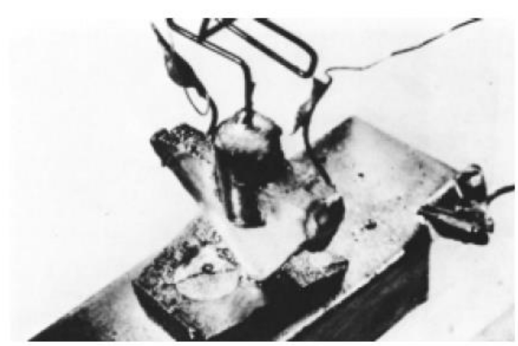


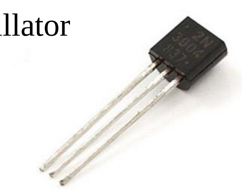
Figure 3.1 The first transistor. (Courtesy Bell Telephone Laboratories.)

Bipolar junction Transistor (BJT):

BJT:

1. It’s a semiconductor device that can amplify electrical signals such as radio or television signals.

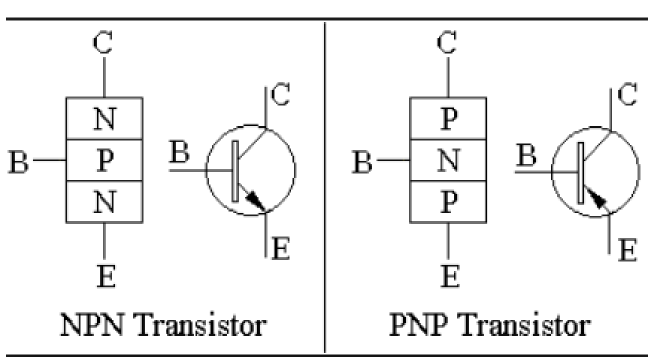
2. Its essential ingredient of every electronic circuits; from the simplest amplifier or oscillator to the most elaborate digital computer.



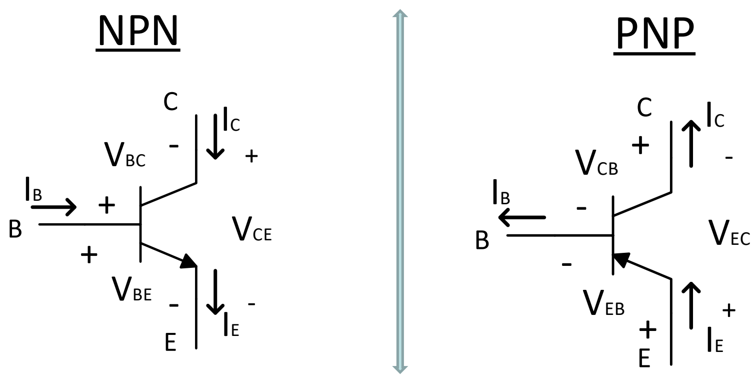
3. It’s a three terminal device; Base, Emitter, and Collector.

There are two type of BJT:

- **npn** type
- **pnp** type



Transistor structure:



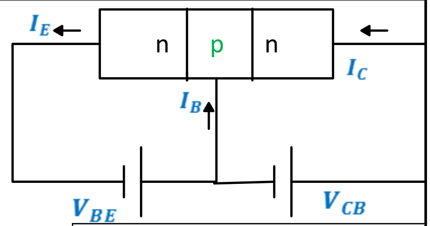
Transistor biasing:

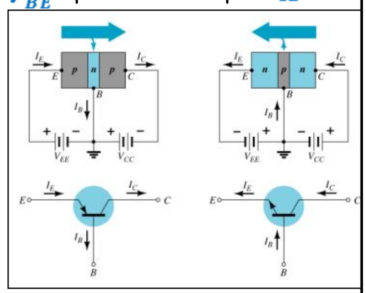
- ✓ In order to operate properly as an amplifier, it's necessary to correctly bias the two pn-junctions with external voltages.
- ✓ Depending upon external bias voltage polarities used; the transistor works in one of **four regions** (modes).
- ✓ For transistor to be used as an Active device **(Amplifier);** the emitter-base junction must be forward bias, while the collector-base junction must be reverse biased.

npn transistor modes of operation

Junction/ Mode	BE	BC	Remarks
Saturation Mode	Forward	Forward	Equivalent to short circuit Ic=Ic(sat) Vce=Vce(sat)=~ 0.2V
Active Mode (Linear Region)	Forward	Reverse	Ic proportional to Ib Vce defined by circuit
Cut-off Mode	Reverse	Reverse	Equivalent to open circuit Ic=Ib=0 Vce defind by circuit
Inverse Mode	Reverse	Forward	Rarely used and will not be discussed in this course

In active region





- ✓The base region is thin and lightly doped
- ✓The base-emitter junction is forward biased, thus the depletion region at this junction **is reduced**.
- ✓The base-collector junction is reverse biased, thus the depletion region at this junction **is increased**.
- ✓The forward biased BE-junction causes the electrons in the n-type emitter to flow toward the base; this constitutes the emitter current I_E.
- ✓As these electrons flow through the P-type base; they tend to recombine with holes in p-type base.

- ✓Since the base region is **lightly doped**; very few of the electrons injected into the base from the emitter recombine with holes to constitute base current I_B and the remaining large number of electrons cross the base and move through the collector region to the positive terminal of the external DC source; this constitute collector current I_C
- ✓There is another component for I_C due to the minority carrier; I_{CBO} which will be ignored
- ✓$I_C = \alpha I_E + I_{CBO}$

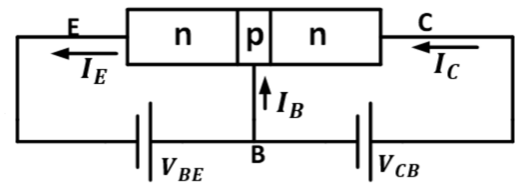
Minority

Majority

$0.998 > \alpha > 0.9$

In active region:

(for info only)



$$I_C = \alpha I_E + I_{CBo}$$

$$I_E = I_C + I_B$$

$$I_C = \alpha(I_C + I_B) + I_{CBo}$$

❖ $I_C = \frac{\alpha}{1-\alpha} I_B + \frac{1}{1-\alpha} I_{CBo}$

Let Beta, $\beta = \frac{\alpha}{1-\alpha}$

❖ $I_C = \beta I_B + (\beta + 1) I_{CBo}$

$$I_C = \beta I_B + I_{CEo}$$

$$\beta = \frac{\alpha}{1-\alpha}$$

If $\alpha = 0.99$ → $\beta = 99$

If $\alpha = 0.995$ → $\beta = 199$

Approximate relationships:

Will be used in this course

$$I_E = I_C + I_B$$

$$I_C \cong \alpha I_E \cong I_E$$

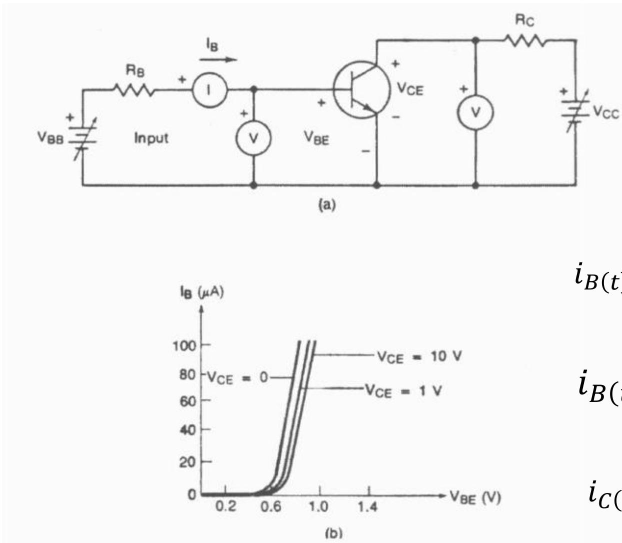
$$I_C \cong \beta I_B$$

$$I_E \cong (\beta+1) I_B$$

$\beta = \frac{\alpha}{1-\alpha}$ $\alpha = \frac{\beta}{\beta+1}$

- https://www.youtube.com/watch?v=7ukDKVHnac4

Input characteristic curve (Common Emitter):

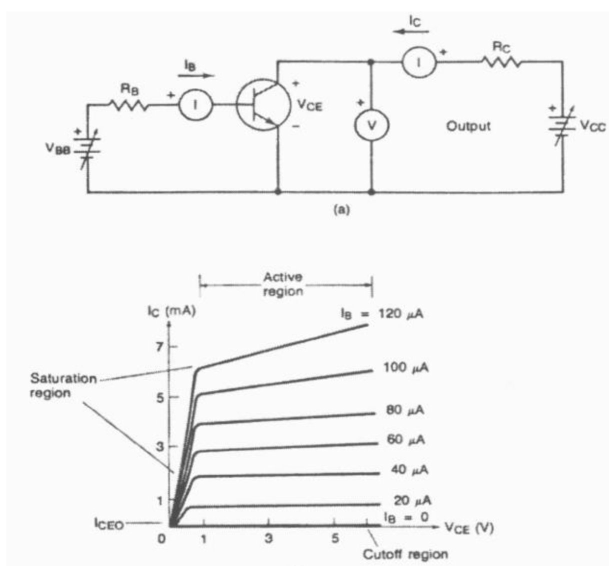


$$i_{B(t)} = I_{Bo}\left(e^{\frac{V_{BE}(t)}{\eta V_T}} - 1\right)$$

$$i_{B(t)} \cong I_{Bo}\left(e^{\frac{V_{BE}(t)}{\eta V_T}}\right)$$

$$i_{C(t)} \cong I_S\left(e^{\frac{V_{BE}(t)}{\eta V_T}}\right)$$

Output characteristic curve:

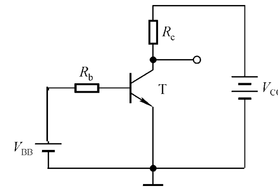


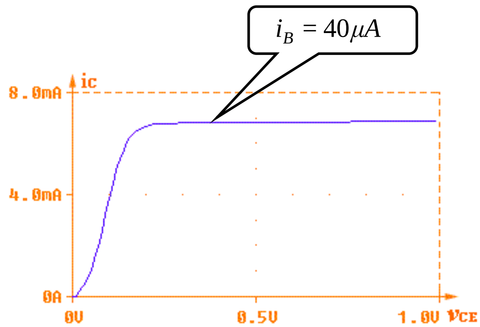
Basic BJT Amplifiers Circuits

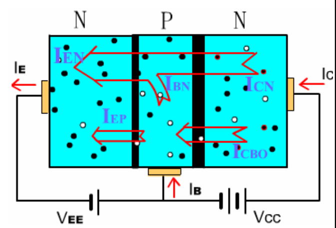
C-E Circuits I-V Characteristics

Collector characteristic (output characteristic)

$$i_C = f_{(V_{CE})}\Big|_{i_B=C}$$







Basic BJT Amplifiers Circuits

C-E Circuits I-V Characteristics

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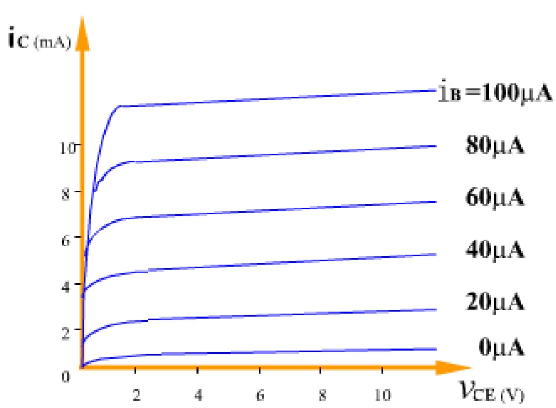


Summary

1. In the cutoff region :

$I_B = I_C = I_E = 0$

2. In the active region :

$I_C = \alpha I_E$

$I_C = \beta I_B$

$I_E = (\beta+1) I_B$

$V_{BE} = 0.7\ v$, Si , npn

$V_{BE} = -0.7\ v$, Si , pnp

$V_{CE} > V_{CE,sat} = 0.2\ v$, Si , npn

$V_{CE} < V_{CE,sat} = -0.2\ v$, Si , pnp

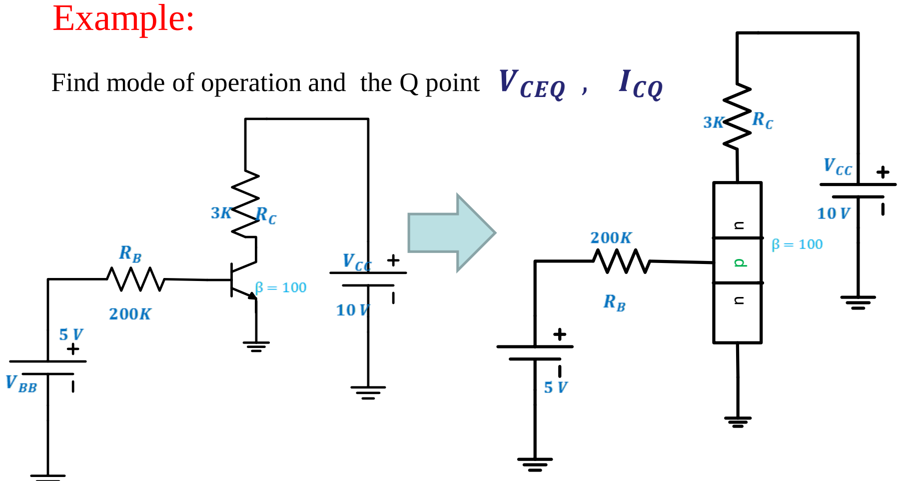
3. In the saturation region :

$V_{CE} = V_{CE,sat}$

$VBE = 0.8\ V$, Si , npn
$VBE = -0.8\ V$, Si , pnp

Example:

Find mode of operation and the Q point V_{CEQ} , I_{CQ}



Since the base emitter junction is forward bias; the transistor could be either in the active or the saturation region

➢Assume that the transistor in the active region:

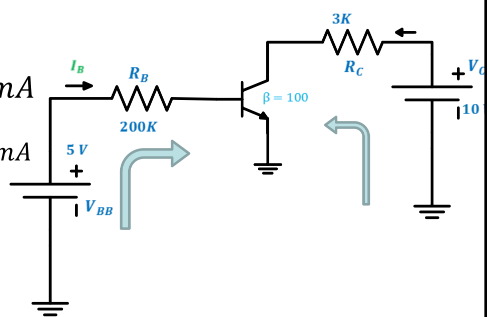
KVL: $5 = 200k\, I_B + V_{BE}$

$$I_B = \frac{5-0.7}{200k} = 0.0215\ mA$$

$I_C = \beta\, I_B = 100 * 0.0215 = 2.15\ mA$

KVL: $10 = R_C I_C + V_{CE}$

$$V_{CE} = 10 - R_c I_c$$



❖$V_{CE} = 10 - 3k * 2.15mA = 3.55\ Volt$

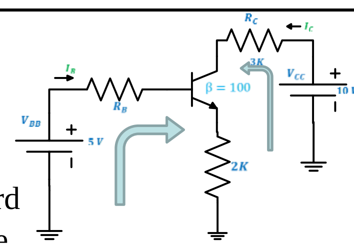
Since

$V_{CE} > V_{CE,sat}$ >>> The transistor is in the active region

➢$\boldsymbol{V_{CEQ} = 3.55\ \ Volt}$
➢$\boldsymbol{I_{CQ} = 2.15\ mA}$

Example

Find the Q point V_{CEQ} , I_{CQ}



Solution:

Since the base emitter junction is forward bias ; the transistor could be either in the active or the saturation region

➢Assume that the transistor in the active region

KVL: $5 = 200k\, I_B + V_{BE} + 2k\, I_E$

$I_E = (\beta+1) I_B$

$$I_B = \frac{5-0.7}{200k + 101 * 2k} = 0.0107\ mA$$

$I_C = \beta\, I_B = 100 * 0.0107 = 1.07\ mA$

KVL: $10 = R_C I_C + V_{CE} + R_E I_E$

$V_{CE} = 10 - R_c I_c - R_E I_E$

❖$V_{CE} = 4.63\ Volt$

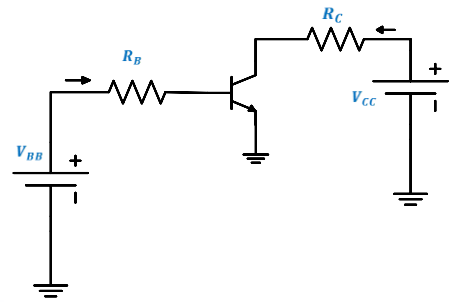
Since

$V_{CE} > V_{CE,sat}$ >>> The transistor is in the active region

➢$\boldsymbol{V_{CEQ} = 4.63\ Volt}$
➢$\boldsymbol{I_{CQ} = 1.07\ \ mA}$

Second Method

1)In the active region:



$$I_B = \frac{V_{BB} - V_{BE}}{R_B}$$

$$I_C = \beta I_B$$

$$V_{CE} = V_{CC} - R_c I_c$$

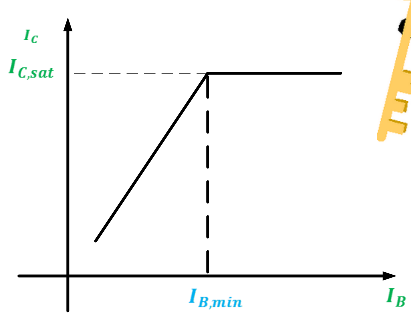
As : $R_B \downarrow$, $I_B \uparrow$, $I_C \uparrow$, $V_{CE} \downarrow$

2) In the saturation region:

$V_{CE} = V_{CE,sat} = 0.2\ v$, Si , npn

$$I_C = I_{C,sat} = \frac{V_{CC} - V_{CE,sat}}{R_C}$$

Let define: $I_B(min) = \frac{I_{C,sat}}{\beta}$

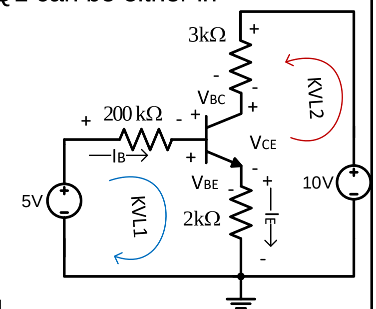


$$I_B(min) = \frac{I_{C,sat}}{\beta}$$

- If $I_B > I_B(min)$ the transistor is in the **Saturation** region.
- If $I_B < I_B(min)$ the transistor is in the **Active** region.

OR Second method: Assume Saturation

- 1) Since BE junction is forward biased ==> Q1 can be either in Active (Linear) or Saturation mode
- Assume it is in **saturation mode**:



$$10 - I_{C(sat)}.3k\Omega - I_{E(sat)}.2k\Omega = V_{CE(Sat)}$$

$$\text{assume} \quad I_{E(sat)} = I_{C(sat)}$$

$$\therefore I_{C(sat)} = \frac{10-0.2}{5k\Omega} = 1.96 \ \text{mA}$$

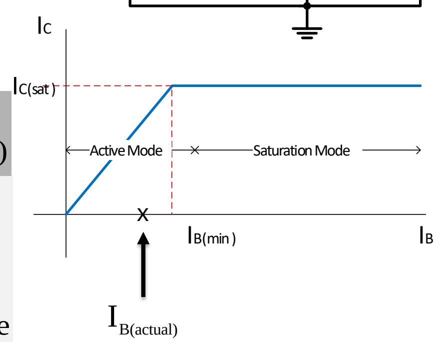
$$I_{B(min)} = \frac{I_{C(sat)}}{\beta} = 19.6 \ \mu A$$

Now we find the actual value of IB

$I_{B(actual)} = 10.7 \ \mu A$ (it was found previously)

since

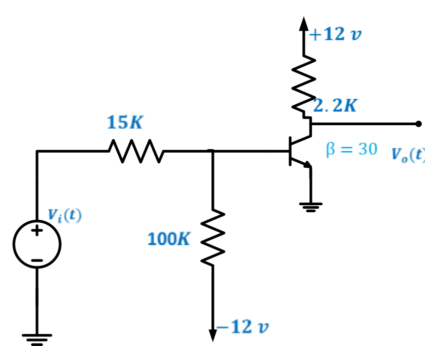
$I_{B(actual)} < I_{B(sat)} = I_{B(min)} \Rightarrow$ the assumption made earlier that BJT in saturation mode is wrong, and actually it is in active mode

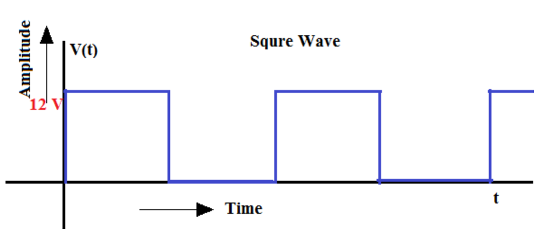


BJT as switch:

Example:

Find $V_o(t)$ for the input given below:

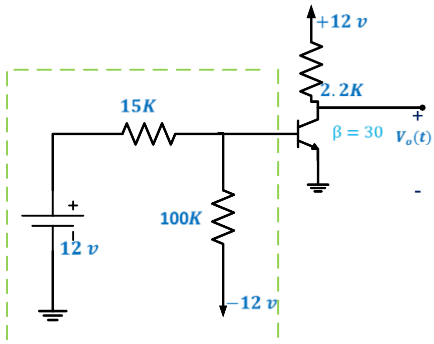


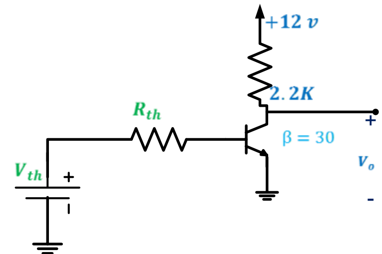


Solution:

❖Let $V_i(t) = +12\ volt$

Calculate V_{th} & R_{th}





$R_{th} = 15k\ //\ 100k = \frac{100k * 15k}{15k + 100k} = 13k$

$V_{th} = 8.9\ volt$ Proof!!

Since the base emitter junction is forward bias; the transistor could be either in the active or the saturation region

➢Assume that the transistor in the saturation region

$$I_C = I_{C,sat} = \frac{V_{CC} - V_{CE,sat}}{R_C} = \frac{12 - 0.2}{2.2k} = 5.36\ mA$$

$$I_B(min) = \frac{I_{C,sat}}{\beta} = \frac{5.36mA}{30} = 0.18mA$$

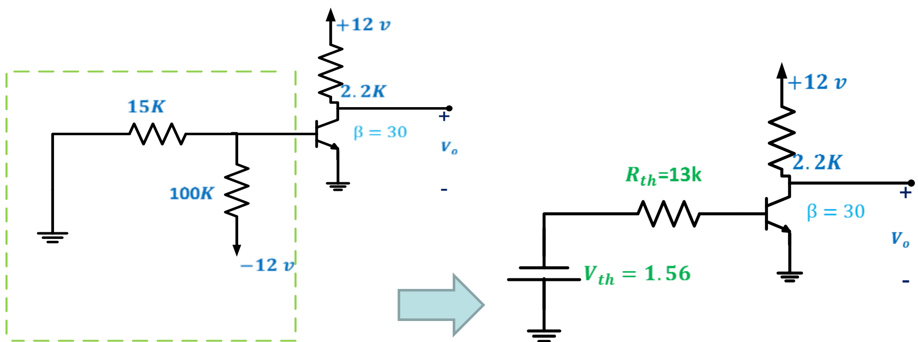
$$I_B = \frac{V_{th} - V_{BE}}{R_{TH}} = \frac{8.9 - 0.8}{13k} = 0.62\ mA$$

Since $I_B > I_B(min)$ the transistor is in the saturation region.

✓$V_o = V_{CE,sat} = 0.2\ volt$

✓$I_C = 5.36\ mA$

❖Let $V_i(t) = 0\ volt$



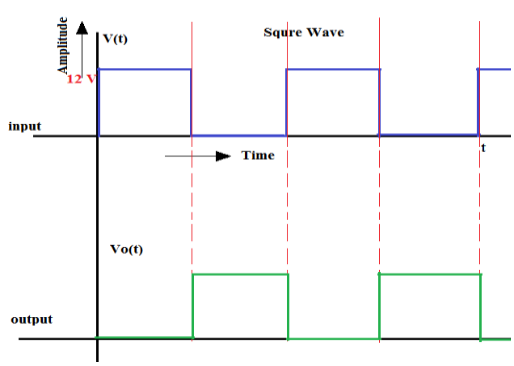
Since $V_{th} = -1.56\ volt$

Base emitter junction is revers biased the transistor in cutoff region

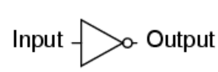
✓$V_o = V_{CE} = 12\ \ volt$

✓$I_C = 0\ mA$

The circuit acts as inverter or not gate



NOT gate truth table



Input	Output
0	1
1	0